

# Kinam Kim

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/9622916/publications.pdf>

Version: 2024-02-01

25  
papers

4,447  
citations

840776

11  
h-index

996975

15  
g-index

26  
all docs

26  
docs citations

26  
times ranked

7035  
citing authors

#	ARTICLE	IF	CITATIONS
1	A fast, high-endurance and scalable non-volatile memory device made from asymmetric Ta <sub>2</sub> O <sub>5</sub> /TaO <sub>2</sub> bilayer structures. <i>Nature Materials</i> , 2011, 10, 625-630.	27.5	1,930
2	Full-colour quantum dot displays fabricated by transfer printing. <i>Nature Photonics</i> , 2011, 5, 176-182.	31.4	997
3	A role for graphene in silicon-based semiconductor devices. <i>Nature</i> , 2011, 479, 338-344.	27.8	667
4	Three-Dimensional 128 Gb MLC Vertical nand Flash Memory With 24-WL Stacked Layers and 50 MB/s High-Speed Programming. <i>IEEE Journal of Solid-State Circuits</i> , 2015, 50, 204-213.	5.4	167
5	Nearly single-crystalline GaN light-emitting diodes on amorphous glass substrates. <i>Nature Photonics</i> , 2011, 5, 763-769.	31.4	156
6	A 0.1- $\mu\text{m}$ 1.8-V 256-Mb Phase-Change Random Access Memory (PRAM) With 66-MHz Synchronous Burst-Read Operation. <i>IEEE Journal of Solid-State Circuits</i> , 2007, 42, 210-218.	5.4	119
7	Neuromorphic electronics based on copying and pasting the brain. <i>Nature Electronics</i> , 2021, 4, 635-644.	26.0	94
8	Integration of lead zirconium titanate thin films for high density ferroelectric random access memory. <i>Journal of Applied Physics</i> , 2006, 100, 051604.	2.5	89
9	1.1 Silicon technologies and solutions for the data-driven world. , 2015, , .		44
10	17.1 A 10nm FinFET 128Mb SRAM with assist adjustment system for power, performance, and area optimization. , 2016, , .		28
11	Dielectric loss peak due to platinum electrode porosity in lead zirconate titanate thin-film capacitors. <i>Applied Physics Letters</i> , 2002, 81, 2436-2438.	3.3	23
12	Twin SONOS Memory With 30-nm Storage Nodes Under a Merged Gate Fabricated With Inverted Sidewall and Damascene Process. <i>IEEE Electron Device Letters</i> , 2004, 25, 317-319.	3.9	22
13	The Smallest Engine Transforming Humanity: The Past, Present, and Future. , 2021, , .		21
14	A 60nm 6Gb/s/pin GDDR5 Graphics DRAM with Multifaceted Clocking and ISI/SSN-Reduction Techniques. , 2008, , .		19
15	Electrical properties of highly reliable plug buffer layer for high-density ferroelectric memory. <i>Applied Physics Letters</i> , 2002, 80, 2377-2379.	3.3	11
16	A novel multi-channel field effect transistor (McFET) on bulk Si for high performance sub-80nm application. , 0, , .		11
17	Enhanced data retention of damascene-finFET DRAM with local channel implantation and >100< fin surface orientation engineering. , 0, , .		10
18	Is quantum capacitance in graphene a potential hurdle for device scaling?. <i>Nano Research</i> , 2014, 7, 453-461.	10.4	9

#	ARTICLE	IF	CITATIONS
19	A 0.18 $\mu$ m 3.0 V 64 Mb non-volatile phase-transition random-access memory (PRAM). , 0, , .		7
20	A VISION OF FRAM AS A FUSION MEMORY. Integrated Ferroelectrics, 2008, 96, 100-111.	0.7	6
21	Effect of the Bottom Electrode Contact (BEC) on the phase transformation of N <sub>2</sub> doped Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> (N-GST) in a Phase-change Random Access Memory. Materials Research Society Symposia Proceedings, 2004, 830, 25.	0.1	5
22	Highly sensitive and reliable X-ray detector with HgI <sub>2</sub> photoconductor and oxide drive TFT. , 2011, , .		4
23	Dual gate photo-thin film transistor with high photoconductive gain for high reliability, and low noise flat panel transparent imager. , 2011, , .		4
24	Guest editorial special section on issues related to semiconductor manufacturing at technology nodes below 70 nm. IEEE Transactions on Semiconductor Manufacturing, 2002, 15, 133-136.	1.7	2
25	Enhanced write performance of a 64Mb phase-change random access memory. , 0, , .		2